

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

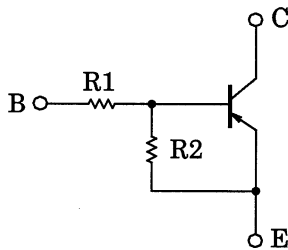
RN2107, RN2108, RN2109

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications

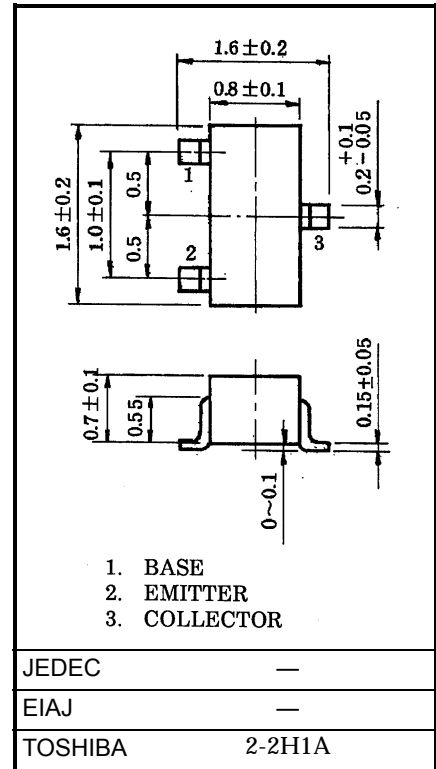
Unit in mm

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN1107~RN1109

Equivalent Circuit and Bias Resister Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2107	10	47
RN2108	22	47
RN2109	47	22



Weight: 2.4mg

Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristic	Symbol	Rating	Unit		
Collector-base voltage	RN2107~RN2109	V_{CB0}	-50	V	
Collector-emitter voltage		V_{CE0}	-50	V	
Emitter-base voltage	RN2107	V_{EB0}	-6	V	
			RN2108		-7
			RN2109		-15
Collector current	RN2107~RN2109	I_C	-100	mA	
Collector power dissipation		P_{C^*}	100	mW	
Junction temperature		T_j	150	°C	
Storage temperature range		T_{stg}	-55~150	°C	

*: Total rating

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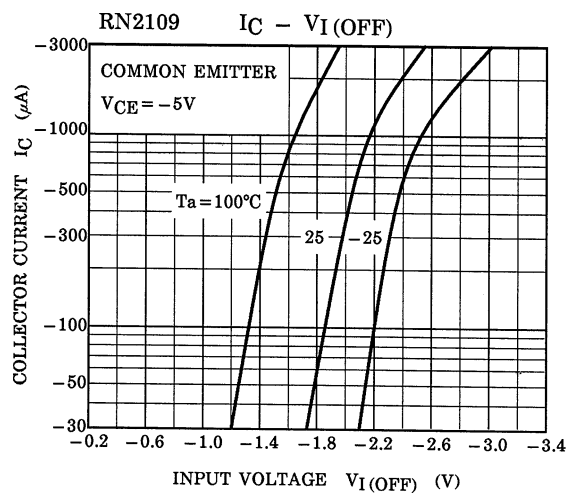
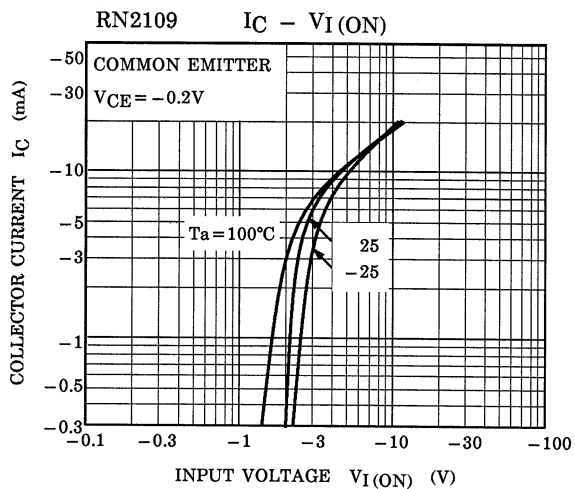
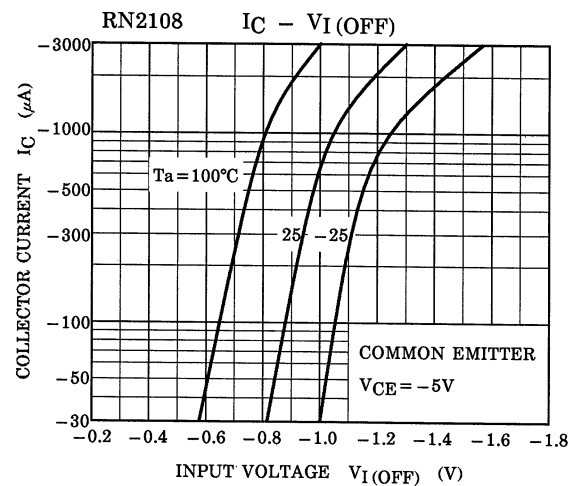
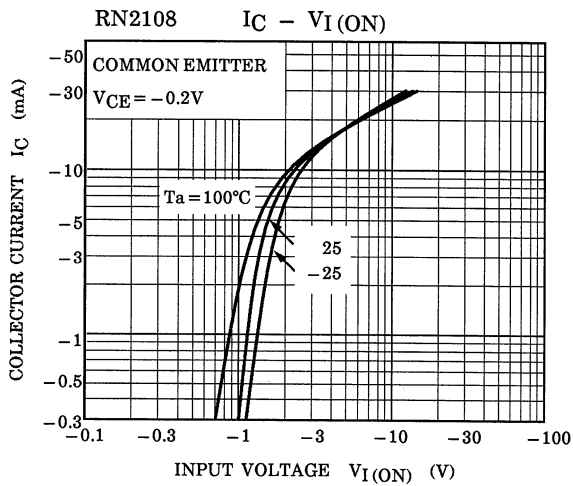
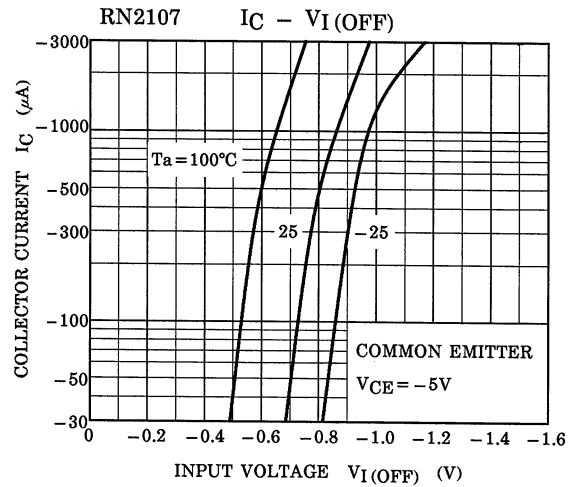
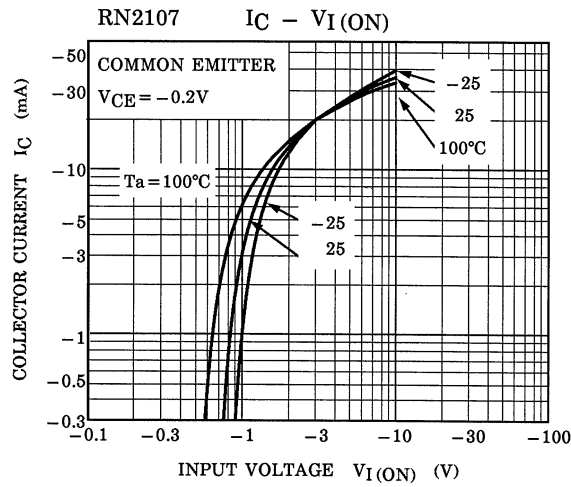
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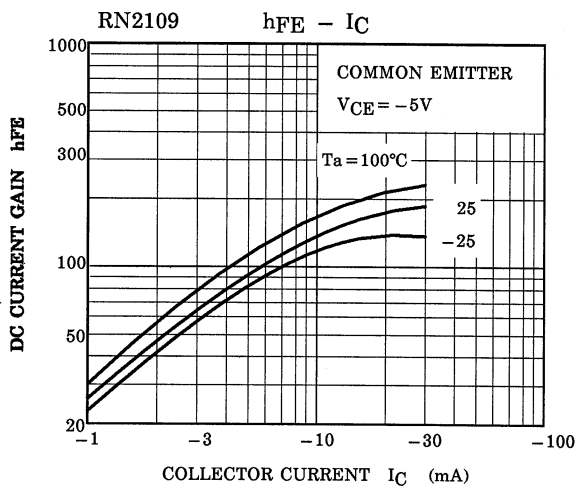
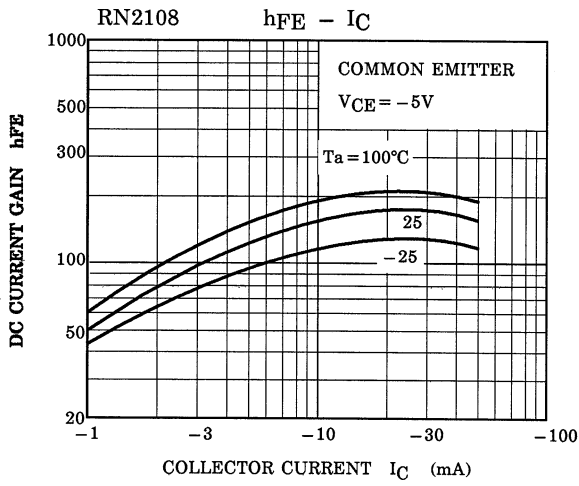
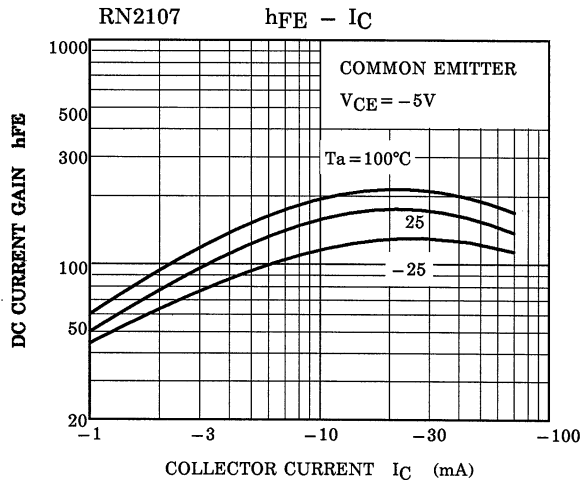
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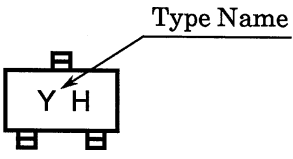
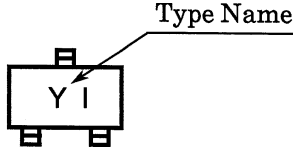
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Electrical Characteristics (Ta = 25°C) (Q1, Q2 Common)

Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN2107 ~RN2109	I_{CBO}	—	$V_{CB} = -50V, I_E = 0$	—	—	-100	nA
		I_{CEO}		$V_{CE} = -50V, I_B = 0$	—	—	-500	nA
Emitter cut-off current	RN2107	I_{EBO}	—	$V_{EB} = -6V, I_C = 0$	-0.081	—	-0.15	mA
	RN2108			$V_{EB} = -7V, I_C = 0$	-0.078	—	-0.145	
	RN2109			$V_{EB} = -15V, I_C = 0$	-0.167	—	-0.311	
DC current gain	RN2107	h_{FE}	—	$V_{CE} = -5V, I_C = -10mA$	80	—	—	—
	RN2108				80	—	—	
	RN2109				70	—	—	
Collector-emitter saturation voltage	RN2107 ~RN2109	$V_{CE(sat)}$	—	$I_C = -5mA, I_B = -0.25mA$	—	-0.1	-0.3	V
Input voltage (ON)	RN2107	$V_{I(ON)}$	—	$V_{CE} = -0.2V, I_C = -5mA$	-0.7	—	-1.8	V
	RN2108				-1.0	—	-2.6	
	RN2109				-2.2	—	-5.8	
Input voltage (OFF)	RN2107	$V_{I(OFF)}$	—	$V_{CE} = -5V, I_C = -0.1mA$	-0.5	—	-1.0	V
	RN2108				-0.6	—	-1.16	
	RN2109				-1.5	—	-2.6	
Transition frequency	RN2107 ~RN2109	f_T	—	$V_{CE} = -10V, I_C = -5mA$	—	200	—	MHz
Collector Output capacitance	RN2107 ~RN2109	C_{ob}	—	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	3	6	pF
Input resistor	RN2107	R1	—	—	7	10	13	kΩ
	RN2108				15.4	22	28.6	
	RN2109				32.9	47	61.1	
Resistor ratio	RN2107	R1/R2	—	—	0.191	0.213	0.232	—
	RN2108				0.421	0.468	0.515	
	RN2109				1.92	2.14	2.35	





Type Name	Marking
RN2107	
RN2108	
RN2109	